

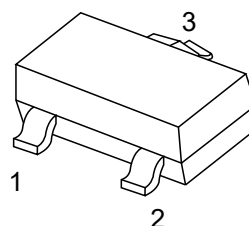
1.Features

- High Collector Current
- SS8550 TRANSISTOR (PNP)
- Complementary to SS8050

2.Pinning Information

Pin	Symbol	Description
1	B	BASE
2	E	EMITTER
3	C	COLLECTOR

SOT-23



3.Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1.5	A
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	417	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}\text{C}$



4. Electrical Characteristics $T_A = 25^\circ\text{C}$

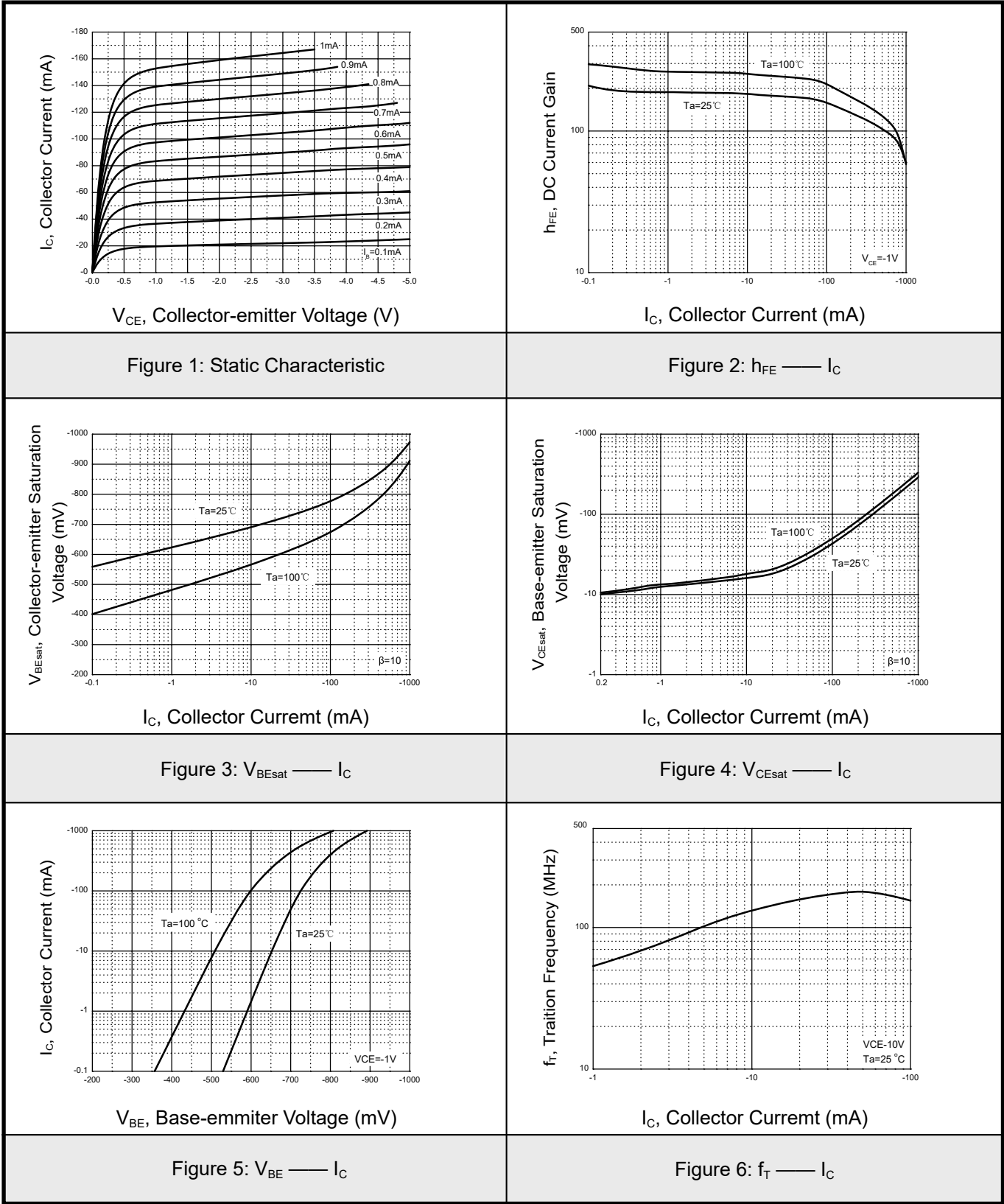
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}$, $I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}$, $I_E = 0$			-100	nA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}$, $I_B = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$	120		400	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}$, $I_C = -800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}$, $I_B = -80\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}$, $I_B = -80\text{mA}$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{V}$, $I_C = -10\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -10\text{V}$, $I_C = -50\text{mA}$, $f = 30\text{MHz}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$			20	pF

5. Classification of $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400
Marking	Y2		

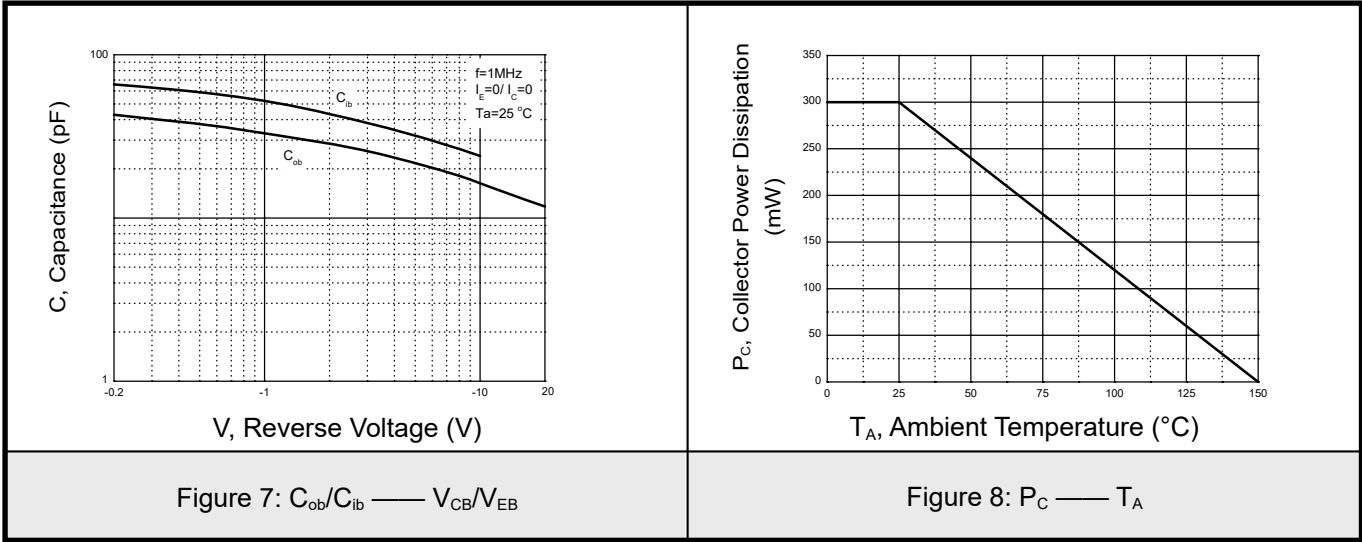


6.1Typical Characteristics



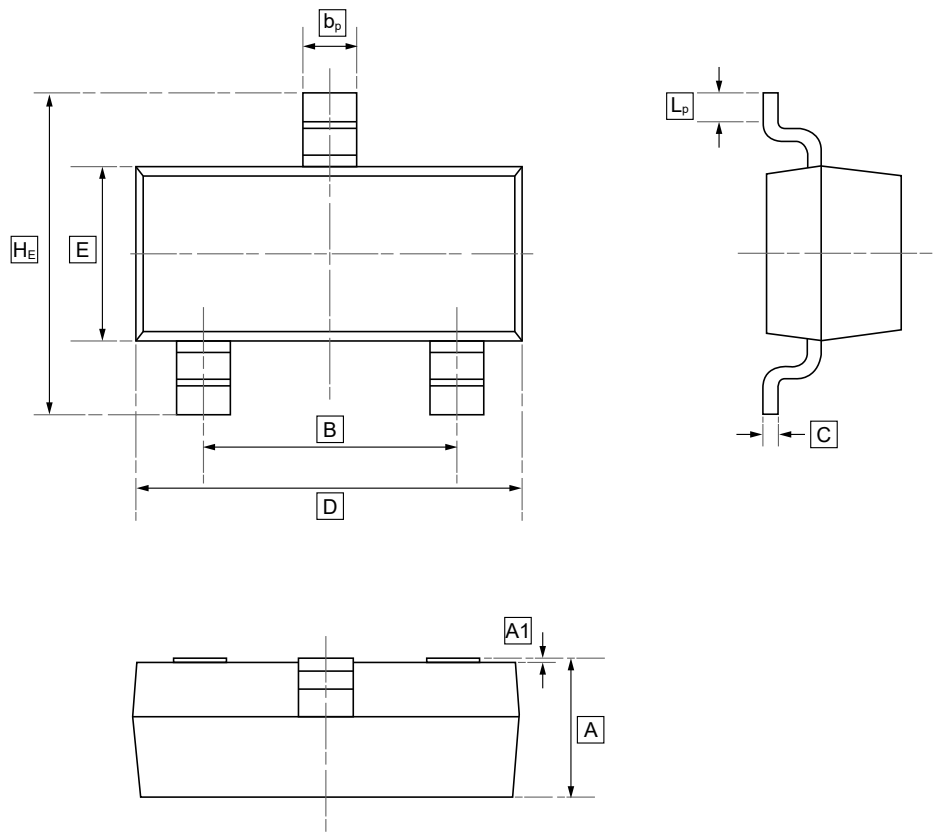


6.2Typical Characterisitics





7.SOT-23 Package Outline Dimensions

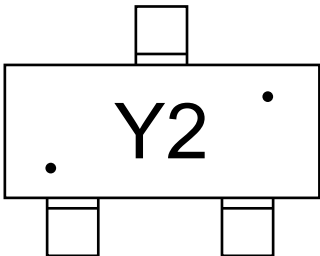


DIMENSIONS (mm are the original dimensions)

Symbol	A	B	b _p	C	D	E	H _E	A1	L _p
Min	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20
Max	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50



8.Ordering information



Order Code	Package	Base QTY	Delivery Mode
UMW SS8550	SOT-23	3000	Tape and reel



9.Disclaimer

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